

ABSTRACT

1 A process for forming a transistor having a gate width of less than 70 nm is
disclosed herein. The process includes E-beam radiation a gate patterned on
a photoresist layer, trimming the gate patterned on the photoresist layer, and
5 etching the gate patterned on the photoresist layer to a polysilicon layer
disposed below the photoresist layer. The gate pattern is E-beam eradiated
by an electron beam.